Abstract

Method for Producing an Epitaxially Coated Semiconductor Wafer

A method for producing an epitaxially coated semiconductor wafer, comprising the following steps in the order specified: (a) depositing an epitaxial layer on one side of a semiconductor wafer; (b) first polishing of the epitaxially coated side of the semiconductor wafer by using a polishing pad with fixed abrasive while supplying a polishing solution which is free of solids;(c) CMP polishing of the epitaxially coated side of the semiconductor wafer by using a soft polishing pad which contains no fixed abrasive, while supplying a polishing agent suspension; (d) depositing another epitaxial layer on the previously epitaxially coated and polished side of the semiconductor wafer.

No Figure.